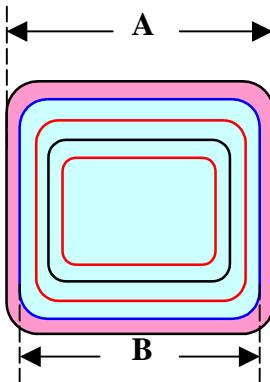


Features : <ul style="list-style-type: none"> * Extremely low forward volts * Guard ring protection * Low reverse leakage current 	Chip size(A):	0.814 * 0.814 mm ²	
	Bond Pad size(B) :	0.686 * 0.686 mm ²	
	Thickness :	300μm ± 20μm	
	Metalization :	Anode Ti/Ni/Ag	
	Metalization :	Cathode Ti/Ni/Ag	
Electrical Characteristics		Sym.	Spec. Limit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C		VF max	0.44
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C		VR min.	23
Minimum Non-repetitive Peak Surge current at 25 °C		IFSM	25
Storage Temperature		TSTG	-65 to +125

HsinChu Headquarter

5F, No. 11, Park Avenue II,
 Science-Based Industrial Park,
 HsinChu City, Taiwan
 TEL: +886-3-567 9979
 FAX: +886-3-567 9909

Sales & Marketing

11F, No. 306-3, SEC. 1, Ta Tung Road,
 Hsichih, Taipei Hsien 221, Taiwan
 TEL: +886-2-8692 1591
 FAX: +886-2-8692 1596